

Chun-Pok Leung, Reg. No. 41,405, (650) 326-2400 Titled: Process for Depositing a Porous, Low Dielectric Constant Silicon Oxide Film App. No. 09/632,425 Filed: August 4, 2000 Dckt. No. A3024/T28300 Sheet 1 of 9

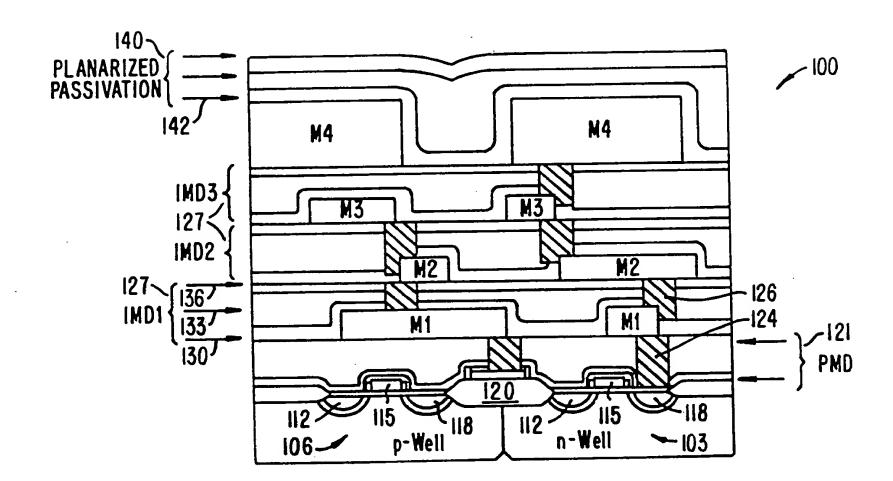


FIG. 1.



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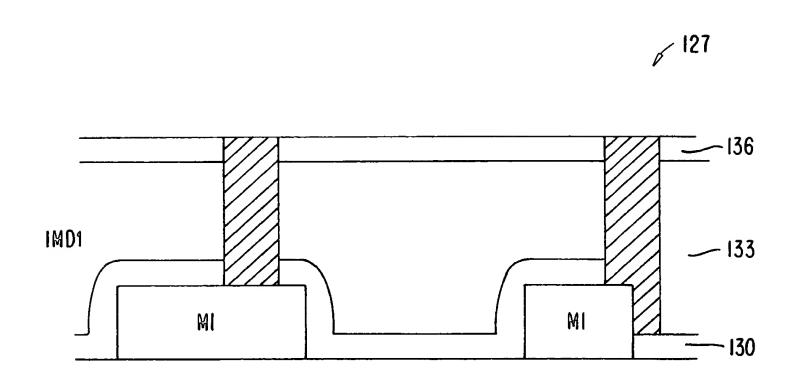


FIG. 2.



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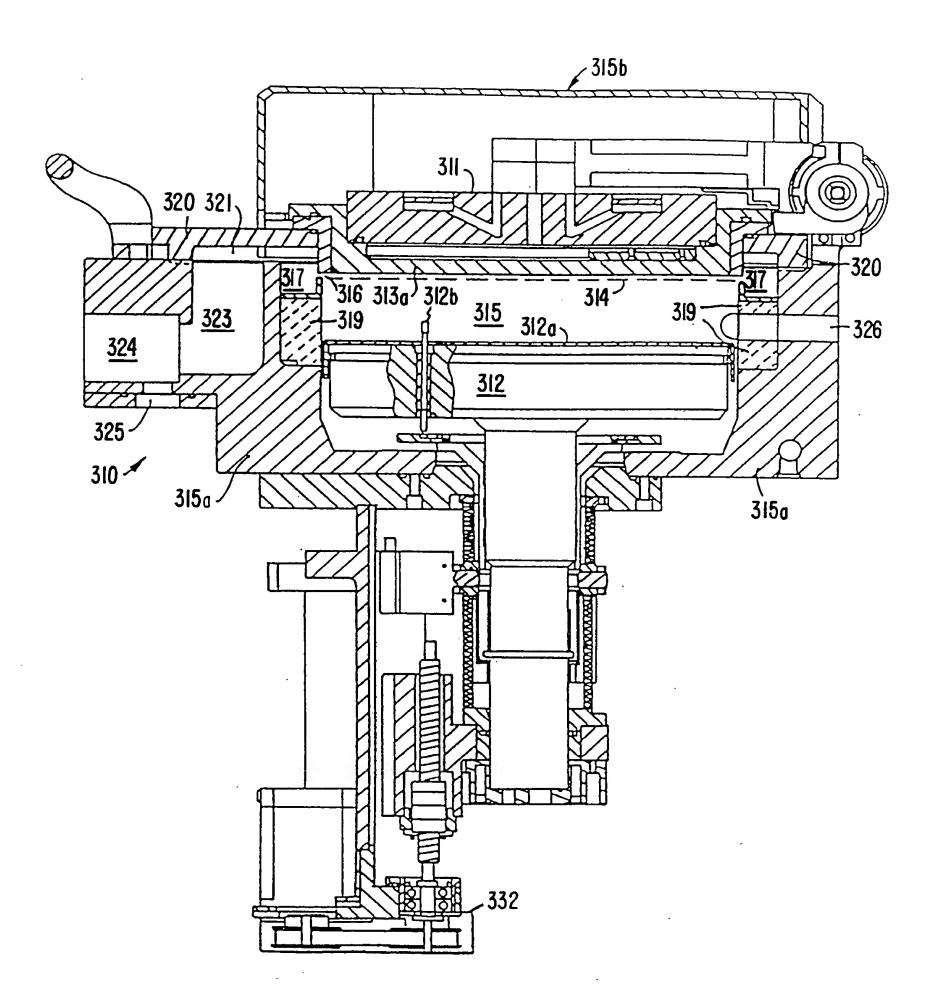


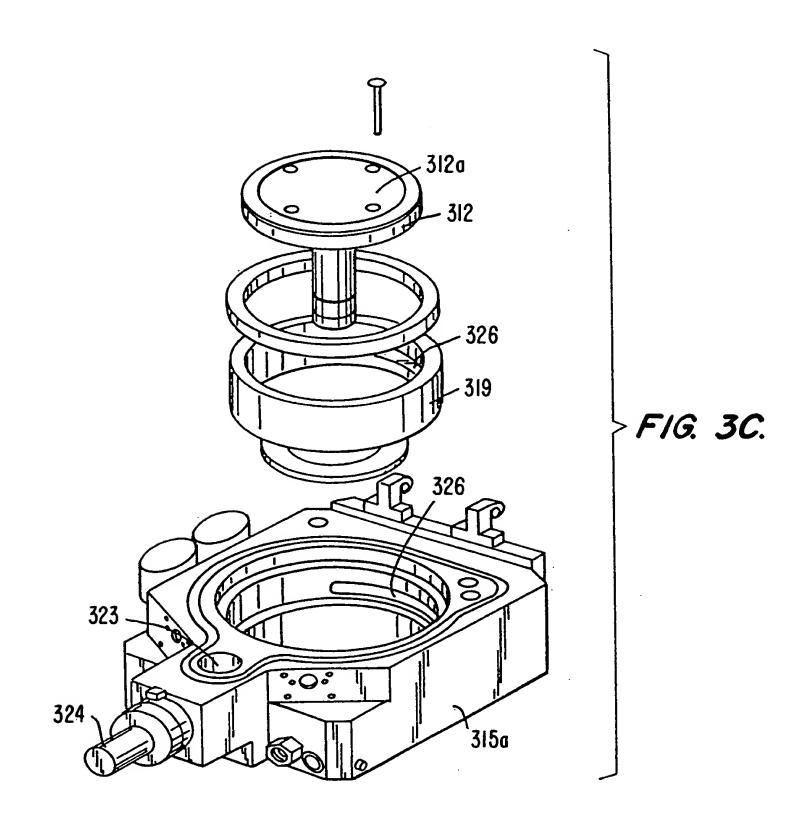
FIG. 3A.



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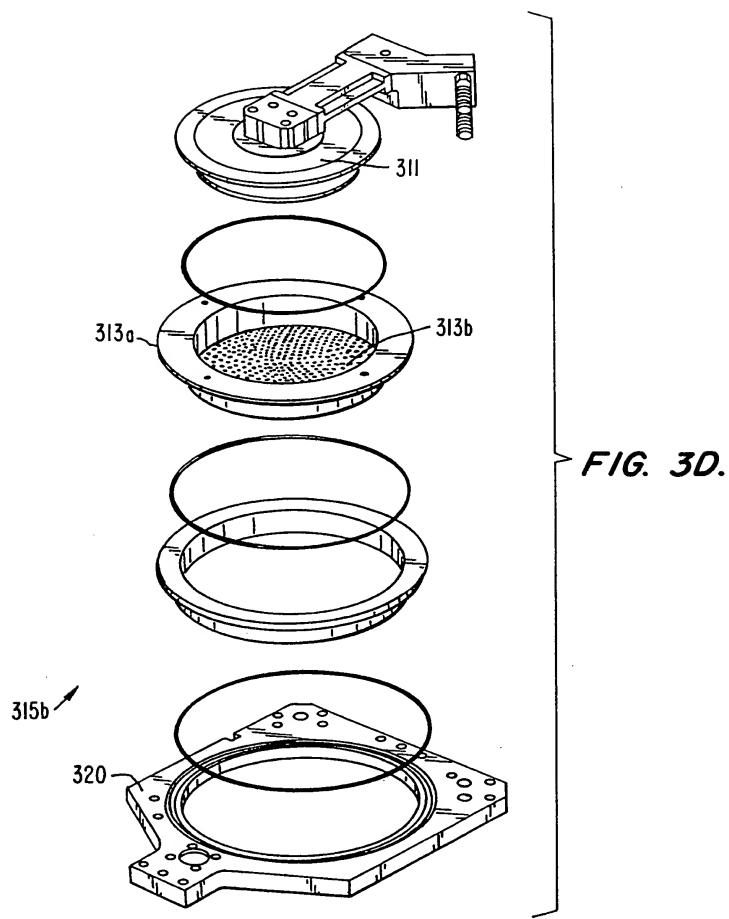


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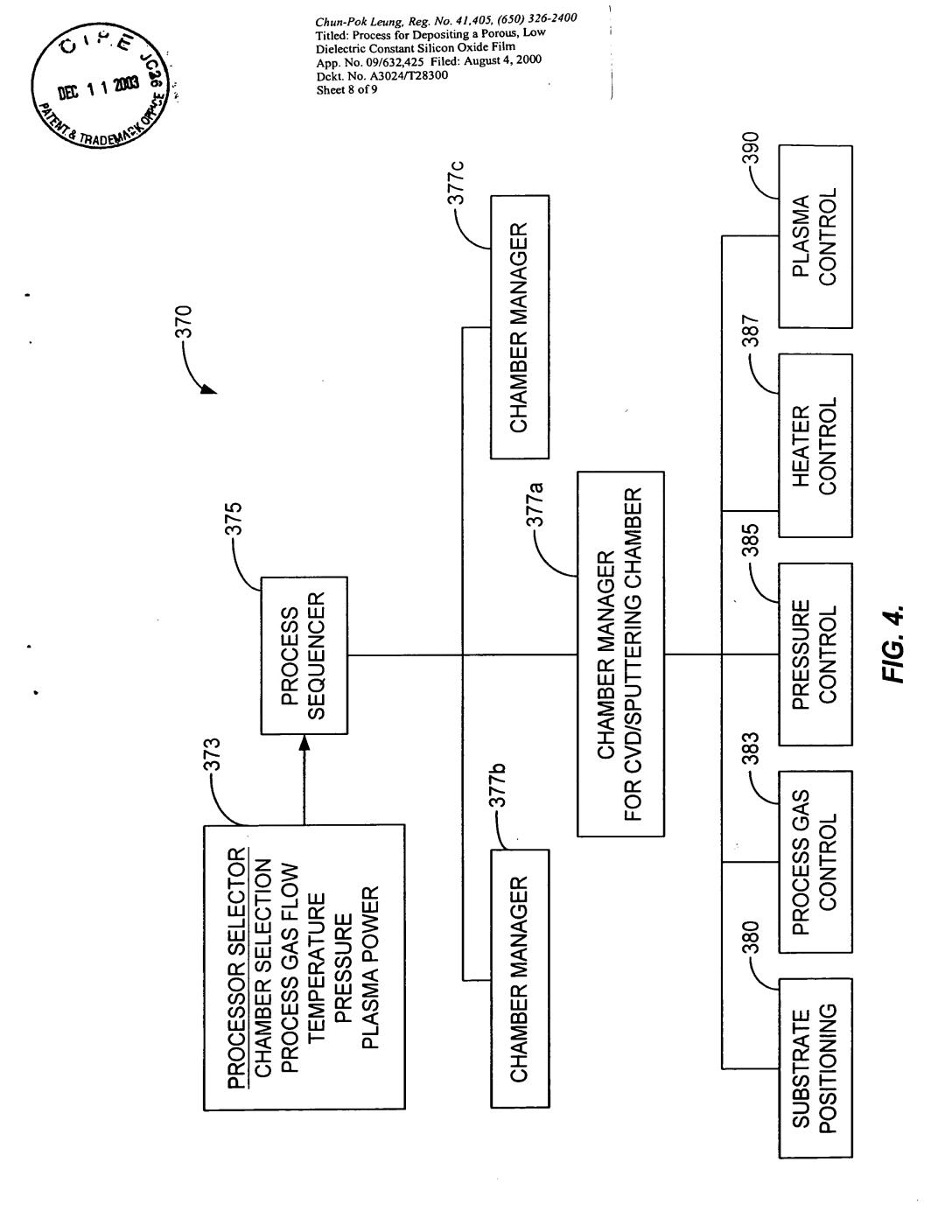




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350a 350ь -350a 350b

FIG. 3E.





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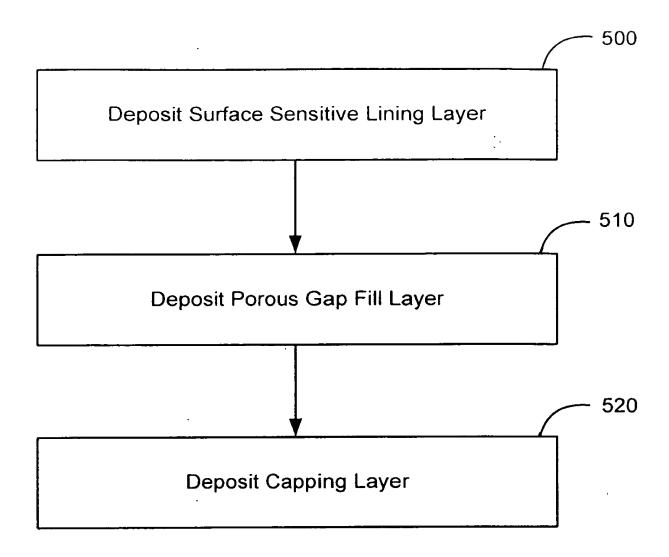


Fig. 5